1[pre]: A method comprising:		
1[a]: in a data storage device that includes a memory having a three-dimensional (3D) memory configuration and including a structure extending through multiple layers of the memory, performing:	12[pre]: A data storage device comprising:	
	12[a]: a memory having a three-dimensional (3D) memory configuration and including a structure extending through multiple layers of the memory;	
1[b]: storing information at the data storage device, the information identifying a location associated with a variation of the structure; and	12[b]: a controller coupled to the memory, wherein the controller is configured to access information that is stored at the memory, the information identifying a location associated with a variation of the structure.	8: The method of claim 1, wherein the data storage device further includes a controller that is operationally coupled to the memory, wherein the information is stored at the memory, and wherein the controller accesses the information from the memory.
1[c]: accessing the information.		
2: The method of claim 1, wherein the structure includes a conductive channel and a charge trap structure, and wherein the variation corresponds to a difference between a first width of the structure at a first distance from a substrate of the memory and a second width of the structure at a second distance from the substrate, the second distance greater than the first distance.	13: The data storage device of claim 12, wherein the structure includes a conductive channel and a charge trap structure, and wherein the variation is a difference between a first width of the structure at a first distance from a substrate of the memory and a second width of the structure at a second distance from the substrate, the second distance greater than the first distance.	
3: measuring a first parameter of a first storage element associated with a first layer of the memory; measuring a second parameter of a second storage element associated with a second layer of the memory; determining whether a difference between the first parameter and the second	14: wherein the controller is further configured to measure a first parameter of a first storage element associated with a first layer of the memory, to measure a second parameter of a second storage element associated with a second layer of the memory, and to determine whether a difference between the first	

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parameter satisfies a threshold.	parameter and the second parameter satisfies a threshold.	
11: The method of claim 1, wherein the memory is a non-volatile memory that is monolithically formed in one or more physical levels of arrays of memory cells having an active area disposed above a silicon substrate, and wherein the data storage device further includes circuitry associated with operation of the memory cells.	20: The data storage device of claim 12, wherein the memory is a non-volatile memory that is monolithically formed in one or more physical levels of arrays of memory cells having an active area disposed above a silicon substrate, and further comprising circuitry associated with operation of the memory cells.	
19: The data storage device of claim 12, wherein the controller is further configured to generate the information in response to determining the location and to store the information at the memory.		

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